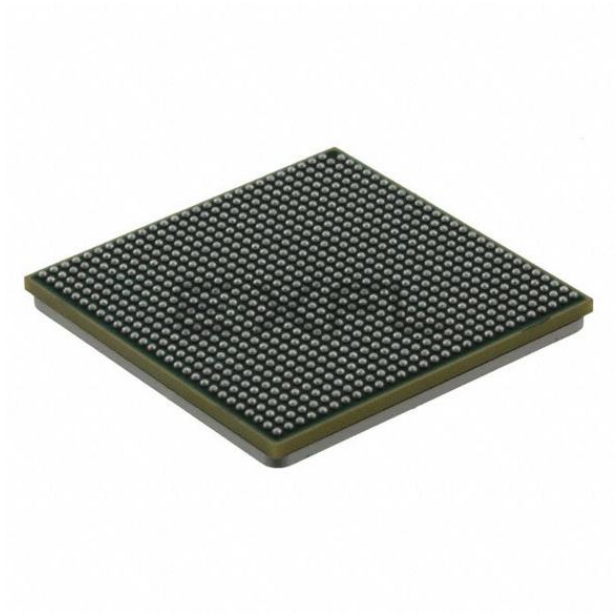

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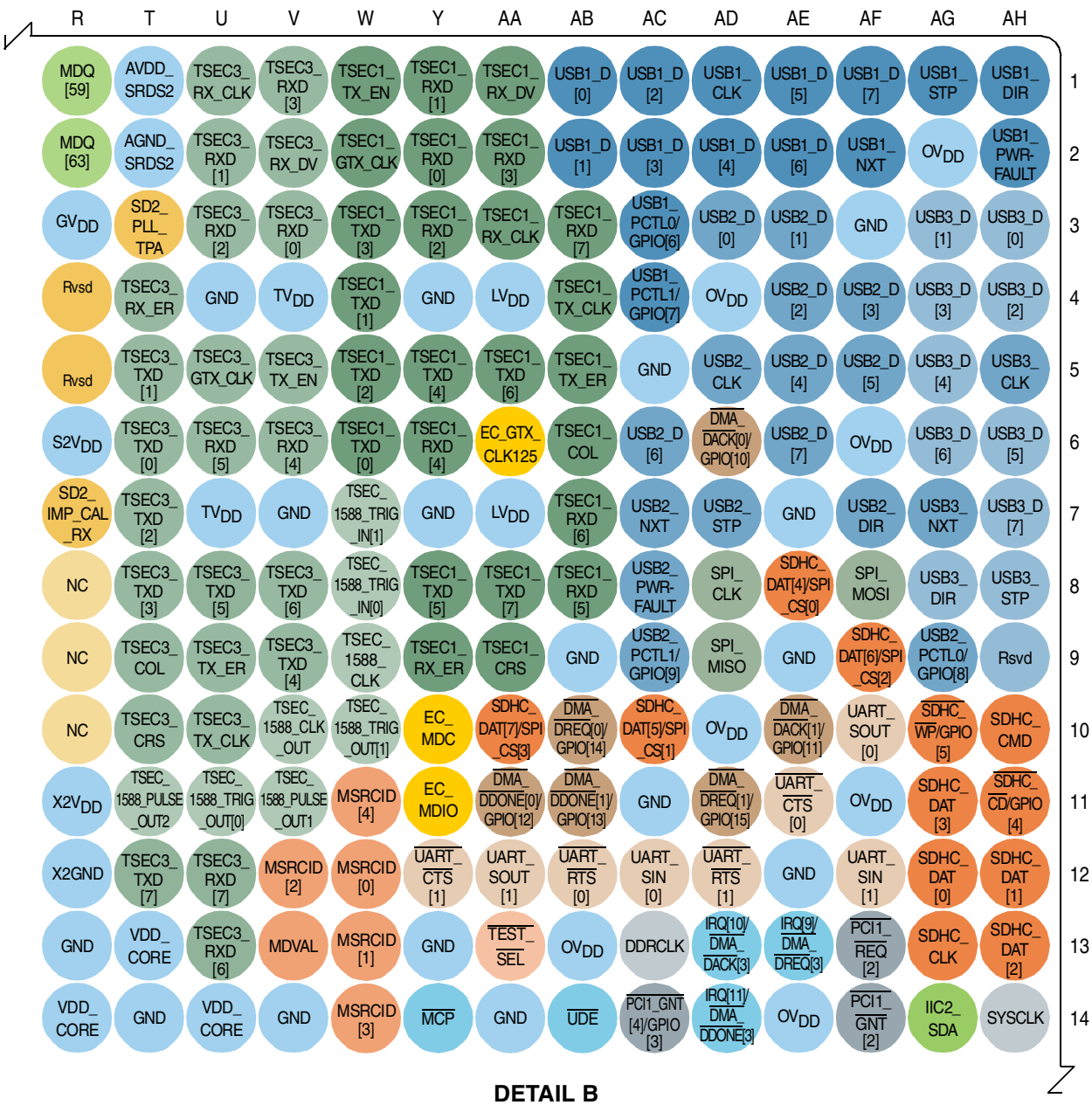
Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	600MHz
Co-Processors/DSP	-
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 (3)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8536avjakga



DETAIL B

Figure 4. Chip Pin Map Detail B

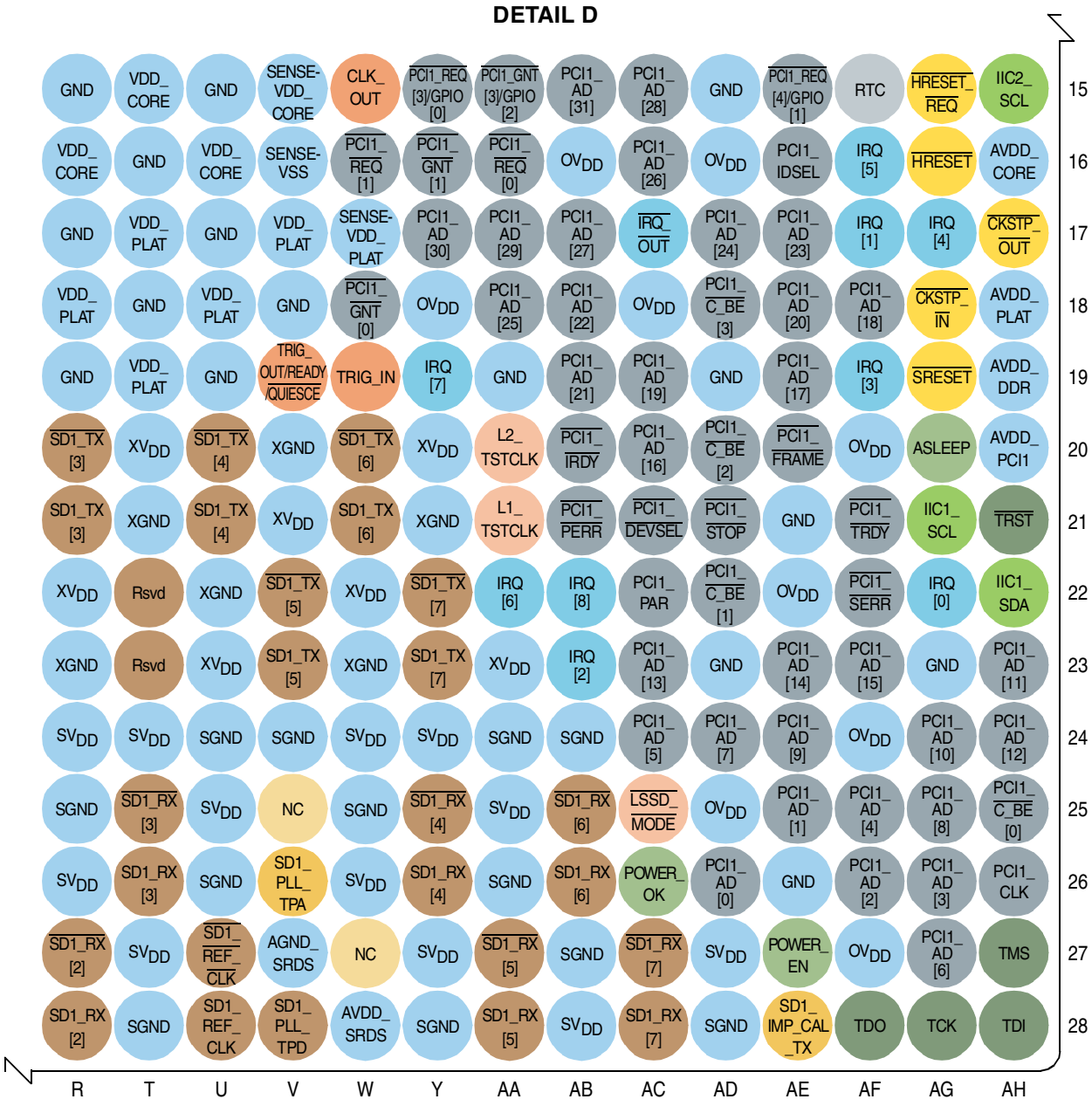


Figure 6. Chip Pin Map Detail D

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
TSEC3_TX_CLK	Transmit clock In	U10	I	TV_{DD}	—
TSEC3_GTX_CLK	Transmit clock Out	U5	O	TV_{DD}	—
TSEC3_CRS	Carrier sense	T10	I/O	TV_{DD}	17
TSEC3_COL	Collision detect	T9	I	TV_{DD}	—
TSEC3_RXD[7:0]	Receive data	U12,U13,U6,V6,V1,U3, U2,V3	I	TV_{DD}	—
TSEC3_RX_DV	Receive data valid	V2	I	TV_{DD}	—
TSEC3_RX_ER	Receive data error	T4	I	TV_{DD}	—
TSEC3_RX_CLK	Receive clock	U1	I	TV_{DD}	—
IEEE 1588					
TSEC_1588_CLK	Clock In	W9	I	LV_{DD}	29
TSEC_1588_TRIG_IN[0:1]	Trigger In	W8,W7	I	LV_{DD}	29
TSEC_1588_TRIG_OUT[0:1]	Trigger Out	U11,W10	O	LV_{DD}	5,9,29
TSEC_1588_CLK_OUT	Clock Out	V10	O	LV_{DD}	5,9,29
TSEC_1588_PULSE_OUT1	Pulse Out1	V11	O	LV_{DD}	5,9,29
TSEC_1588_PULSE_OUT2	Pulse Out2	T11	O	LV_{DD}	5,9,29
eSDHC					
SDHC_CMD	Command line	AH10	I/O	OV_{DD}	29
$\overline{\text{SDHC\_CD}}$/GPIO[4]	Card detection	AH11	I	OV_{DD}	—
SDHC_DAT[0:3]	Data line	AG12,AH12,AH13, AG11	I/O	OV_{DD}	29
SDHC_DAT[4:7] / SPI_CS[0:3]	8-bit MMC Data line / SPI chip select	AE8,AC10,AF9,AA10	I/O	OV_{DD}	29
SDHC_CLK	SD/MMC/SDIO clock	AG13	I/O	OV_{DD}	29
$\overline{\text{SDHC\_WP}}$/GPIO[5]	Card write protection	AG10	I	OV_{DD}	1, 32
eSPI					
SPI_MOSI	Master Out Slave In	AF8	I/O	OV_{DD}	29
SPI_MISO	Master In Slave Out	AD9	I	OV_{DD}	29
SPI_CLK	eSPI clock	AD8	I/O	OV_{DD}	29
SPI_CS[0:3] / SDHC_DAT[4:7]	eSPI chip select / SDHC 8-bit MMC data	AE8,AC10,AF9,AA10	I/O	OV_{DD}	29
DUART					
$\overline{\text{UART\_CTS}}$[0:1]	Clear to send	AE11,Y12	I	OV_{DD}	29
$\overline{\text{UART\_RTS}}$[0:1]	Ready to send	AB12,AD12	O	OV_{DD}	29
UART_SIN[0:1]	Receive data	AC12,AF12	I	OV_{DD}	29

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
TCK	Test clock	AG28	I	OV_{DD}	—
TDI	Test data in	AH28	I	OV_{DD}	12
TDO	Test data out	AF28	O	OV_{DD}	11
TMS	Test mode select	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	Test reset	AH21	I	OV_{DD}	12
DFT					
L1_TSTCLK	L1 test clock	AA21	I	OV_{DD}	19
L2_TSTCLK	L2 test clock	AA20	I	OV_{DD}	19
$\overline{\text{LSSD\_MODE}}$	LSSD Mode	AC25	I	OV_{DD}	19
$\overline{\text{TEST\_SEL}}$	Test select	AA13	I	OV_{DD}	19
Power Management					
ASLEEP	Asleep	AG20	O	OV_{DD}	9,16,22
POWER_OK	Power OK	AC26	I	OV_{DD}	—
POWER_EN	Power enable	AE27	O	OV_{DD}	—
Power and Ground Signals					
OVDD	General I/O supply	Y18,AG2,AD4,AB16, AF6,AC18,AB13,AD10, AE14,AD16,AD25, AF27,AE22,AF11, AF20,AF24	—	OV_{DD}	—
LVDD	GMAC 1 I/O supply	AA7, AA4	Power for TSEC1 interfaces	LV_{DD}	—
TVDD	GMAC 3 I/O supply	V4,U7	Power for TSEC3 interfaces	TV_{DD}	—
GVDD	SSTL2 DDR supply	B1,B11,C7,C9,C14, C17,D4,D6,R3,D15,E2, E8,C24,E18,F5,E14, C21,G3,G7,G9,G11, H5,H12,E22,F15,J10, K3,K12,K14,H14,D20, E11,M1,N5	Power for DDR DRAM I/O	GV_{DD}	—
BVDD	Local bus I/O supply	L23,J18,J23,J19,F20, F23,H26,J21	Power for Local Bus	BV_{DD}	—
SVDD	SerDes 1 core logic supply	M27,N25,P28,R24, R26,T24,T27,U25, W24,W26,Y24,Y27, AA25,AB28,AD27	—	SV_{DD}	—

This table provides the DDR capacitance when GV_{DD}(type) = 1.8 V.

Table 14. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1, 2
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1, 2

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V (for DDR2), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.
2. This parameter is sampled. GV_{DD} = 1.5 V ± 0.075 V (for DDR3), f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.175 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition		Symbol	Min	Max	Unit	Note
Current draw for $MV_{REF}n$	DDR2 SDRAM	I_{MVREFn}	—	1500	μA	1
	DDR3 SDRAM			1250		

1.The voltage regulator for MV_{REF} must be able to supply up to 1500 μA or 1250 uA current for DDR2 or DDR3 respectively.

2.6.2 DDR2 and DDR3 SDRAM Interface AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM Controller interface. The DDR controller supports both DDR2 and DDR3 memories. Please note that although the minimum data rate for most off-the-shelf DDR3 DIMMs available is 800 MHz, JEDEC specification does allow the DDR3 to run at the data rate as low as 606 MHz. Unless otherwise specified, the AC timing specifications described in this section for DDR3 is applicable for data rate between 606 MHz and 667 MHz, as long as the DC and AC specifications of the DDR3 memory to be used are compliant to both JEDEC specifications as well as the specifications and requirements described in this document.

2.6.2.1 DDR2 and DDR3 SDRAM Interface Input AC Timing Specifications

These tables provide the input AC timing specifications for the DDR controller.

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%

Parameter		Symbol	Min	Max	Unit
AC input low voltage	667	V_{ILAC}	—	MV_{REF} – 0.20	V
	<=533		—	MV_{REF} – 0.25	V
AC input high voltage	667	V_{IHAC}	MV_{REF} + 0.20	—	V
	<=533		MV_{REF} + 0.25	—	V

Table 17. DDR3 SDRAM Input AC Timing Specifications for 1.5-V Interface

At recommended operating conditions with GV_{DD} of 1.5 V ± 5%. DDR3 data rate is between 606MHz and 667MHz.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.175	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.175	—	V	—

Table 18. DDR2 and DDR3 SDRAM Interface Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC	t_{CISKEW}	—	—	ps	1, 2
667 MHz	—	–240	240	—	3
533 MHz	—	–300	300	—	—
400 MHz	—	–365	365	—	—

Note:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: t_{DISKEW} =+/-(T/4 - abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. Maximum DDR2 and DDR3 frequency is 667MHz.

This figure shows the DDR2 and DDR3 SDRAM interface input timing diagram.

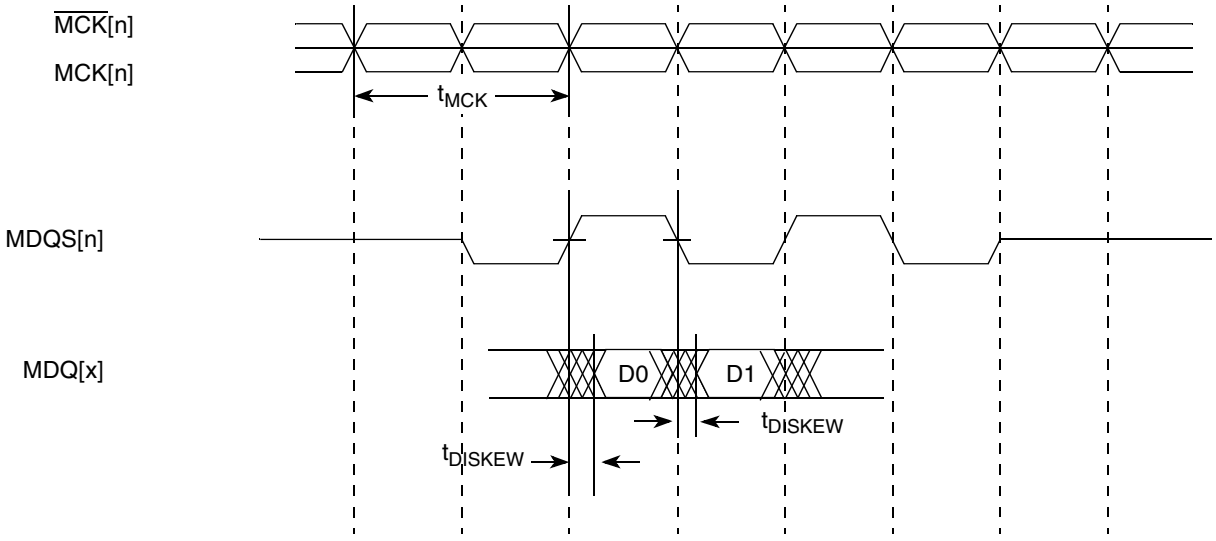


Figure 8. DDR SDRAM Input Timing Diagram

This figure shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

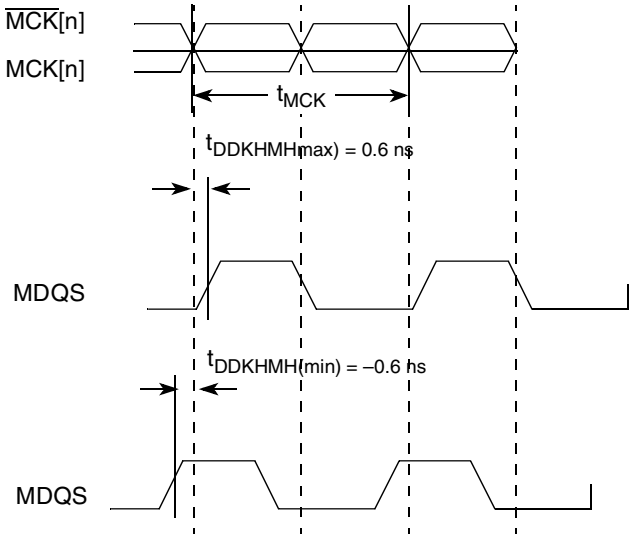


Figure 9. Timing Diagram for tDDKHMH

This figure shows the DDR SDRAM output timing diagram.

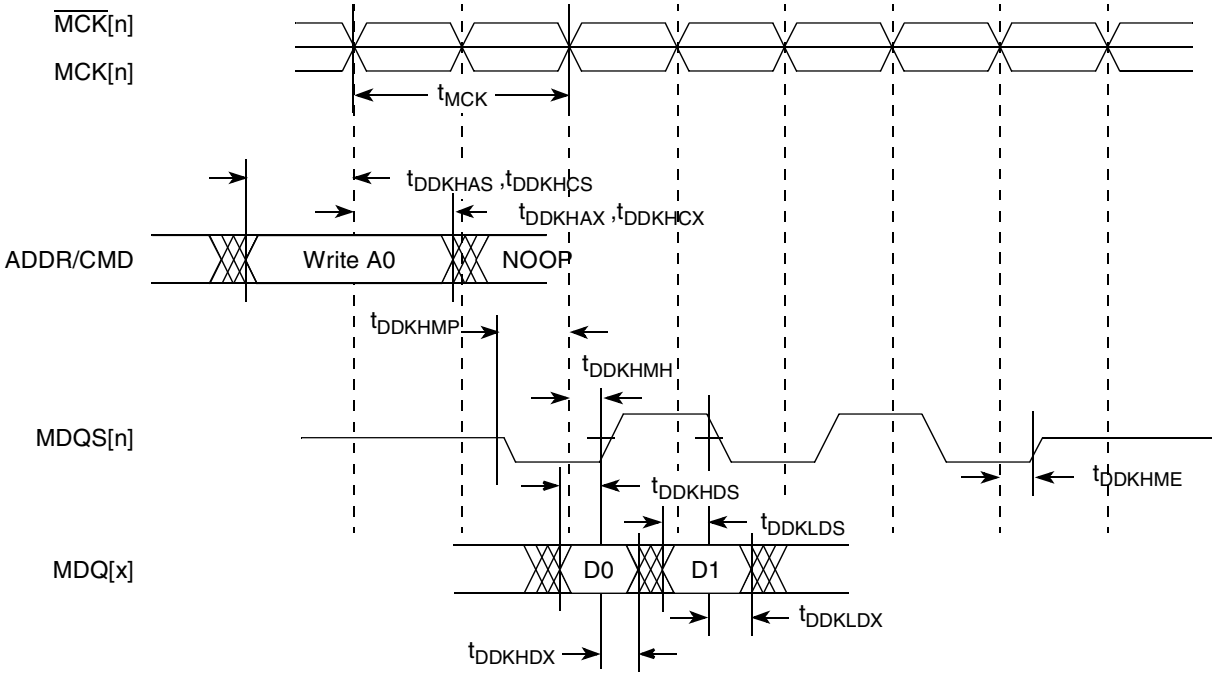


Figure 10. DDR SDRAM Output Timing Diagram

Table 25. RGMII, RTBI, and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.37	2.63	V	1,2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –1.0 mA)	V_{OH}	2.00	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND – 0.3	0.40	V	—
Input high voltage	V_{IH}	1.70	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.70	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	10	µA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	µA	3

Note:

1 LV_{DD} supports eTSECs 1.

2 TV_{DD} supports eTSECs 3.

3 Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

2.9.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI are presented in this section.

2.9.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit clock to synchronously generate transmit data and outputs an echoed copy of the transmit clock back out onto the TSEC*n*_GTX_CLK pin (while transmit data appears on TSEC*n*_TXD[7:0], for example). It is intended that external receivers capture eTSEC transmit data using the clock on TSEC*n*_GTX_CLK as a source-synchronous timing reference. Typically, the clock edge that launched the data can be used, since the clock is delayed by the eTSEC to allow acceptable set-up margin at the receiver. Note that there is relationship between the maximum FIFO speed and the platform speed. For more information see Section 2.4.6, "Platform to FIFO Restrictions."

A summary of the FIFO AC specifications appears in the following tables.

Table 26. FIFO Mode Transmit AC Timing Specification

Parameter/Condition	Symbol	Min	Typ	Max	Unit
TX_CLK, GTX_CLK clock period[2]	t_{FIT}	6.0	8.0	100	ns
TX_CLK, GTX_CLK duty cycle	t_{FITH}	45	50	55	%
TX_CLK, GTX_CLK peak-to-peak jitter	t_{FITJ}	—	—	250	ps

This figure shows the GMII transmit AC timing diagram.

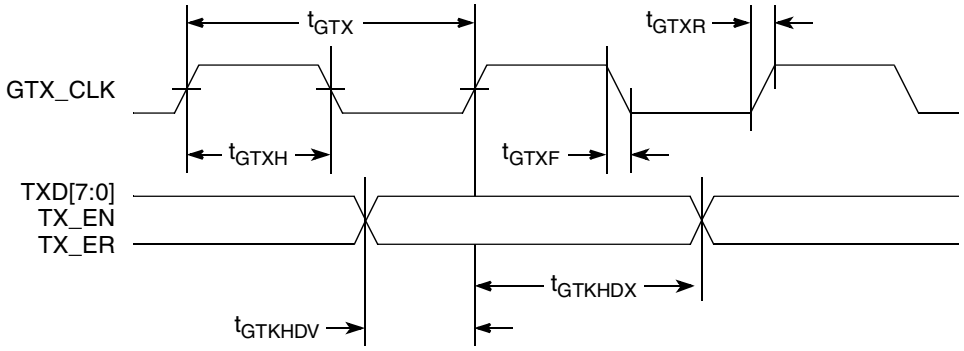


Figure 16. GMII Transmit AC Timing Diagram

2.9.2.2.2 GMII Receive AC Timing Specifications

This table provides the GMII receive AC timing specifications.

Table 29. GMII Receive AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	35	—	65	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0	—	—	ns
RX_CLK clock rise (20%-80%)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time (80%-20%)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load for eTSEC.

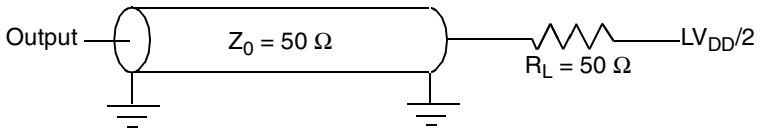


Figure 17. eTSEC AC Test Load

This figure shows the MII receive AC timing diagram.

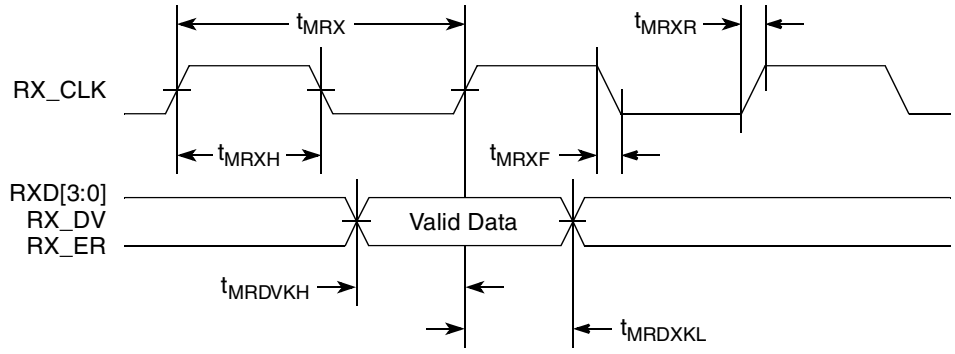


Figure 21. MII Receive AC Timing Diagram

2.9.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

2.9.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 32. TBI Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%
GTX_CLK to TCG[9:0] delay time	t_{TTKHDX}[2]	1.0	—	5.0	ns
GTX_CLK rise (20%–80%)	t_{TTXR}	—	—	1.0	ns
GTX_CLK fall time (80%–20%)	t_{TTXF}	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Data valid t_{TTKHDV} to GTX_CLK Min Setup time is a function of clock period and max hold time. (Min Setup = Cycle time - Max Hold)

This figure shows the TBI transmit AC timing diagram.

This figures provide the AC test load and signals for the USB, respectively.

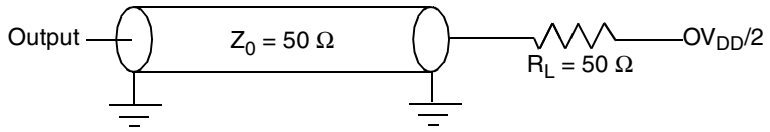


Figure 36. USB AC Test Load

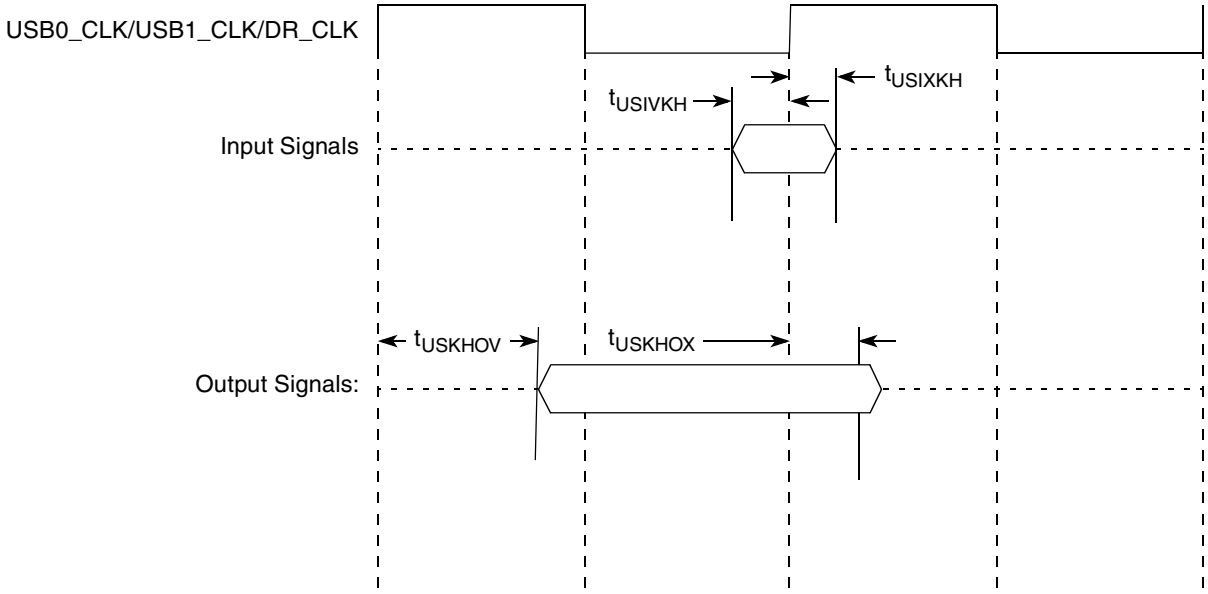


Figure 37. USB Signals

Table 51. Local Bus General Timing Parameters (BV_{DD} = 3.3 V DC) (continued)

Parameter	Symbol [1]	Min	Max	Unit	Notes
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is guaranteed with LBCR[AHD] = 0.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

This table describes the general timing parameters of the local bus interface at BV_{DD} = 2.5 V DC.

Table 52. Local Bus General Timing Parameters (BV_{DD} = 2.5 V DC)

Parameter	Configuration	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	—	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	—	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	$t_{LBKSKEW}$	—	150	ps	7
Input setup to local bus clock (except LUPWAIT)	—	$t_{LBIVKH1}$	1.9	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	$t_{LBIVKH2}$	1.8	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	—	$t_{LBIXKH1}$	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	—	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	—	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	—	$t_{LBKHOV1}$	—	2.4	ns	—
Local bus clock to data valid for LAD/LDP	—	$t_{LBKHOV2}$	—	2.5	ns	3
Local bus clock to address valid for LAD	—	$t_{LBKHOV3}$	—	2.4	ns	3
Local bus clock to LALE assertion	—	$t_{LBKHOV4}$	—	2.4	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	—	$t_{LBKHOX1}$	0.8	—	ns	3

This figures show the local bus signals.

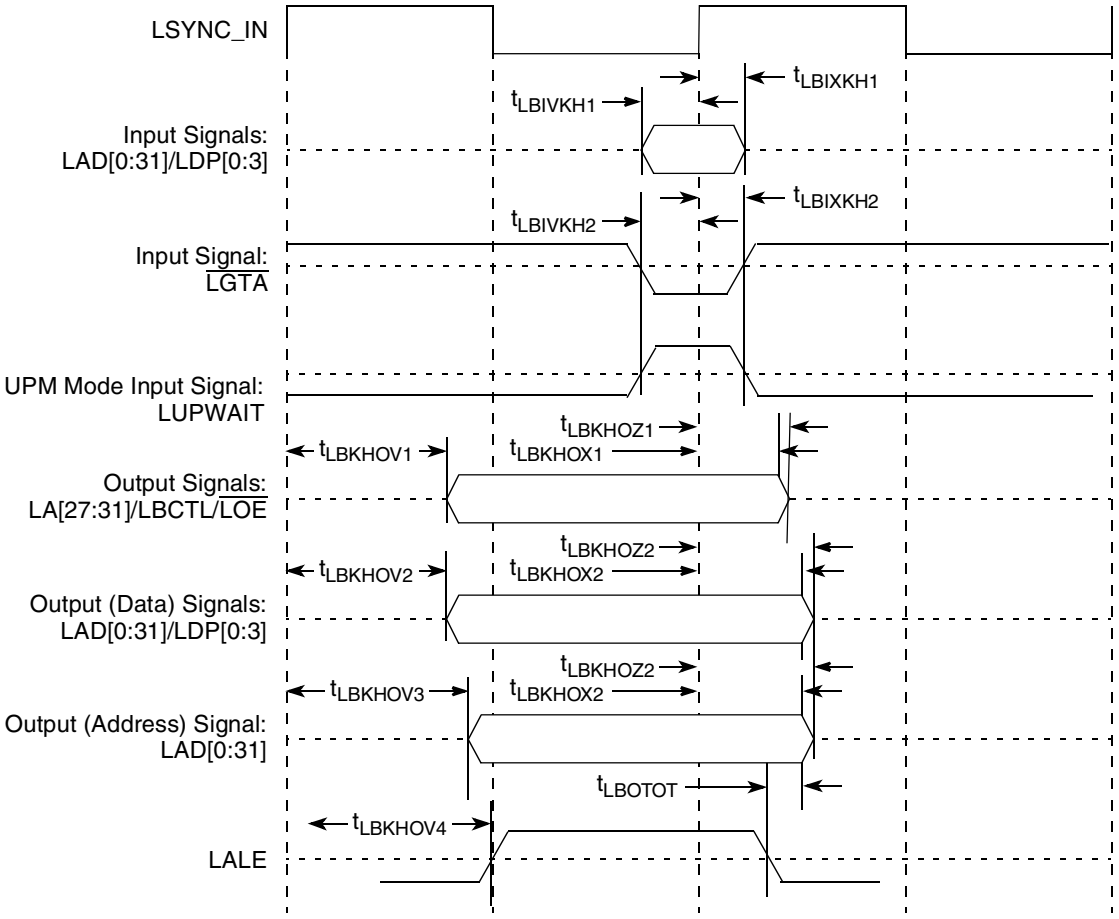


Figure 39. Local Bus Signals, Non-Special Signals Only (PLL Enabled)

NOTE

In PLL bypass mode, some signals are launched and captured on the opposite edge of LCLK[n] to that used in PLL Enable Mode. In this mode, output signals are launched at the falling edge of the LCLK[n] and inputs signals are captured at the rising edge of LCLK[n] with the exception of LGTA/LUPWAIT (which is captured at the falling edge of the LCLK[n]).

This figure shows the PCI output AC timing conditions.

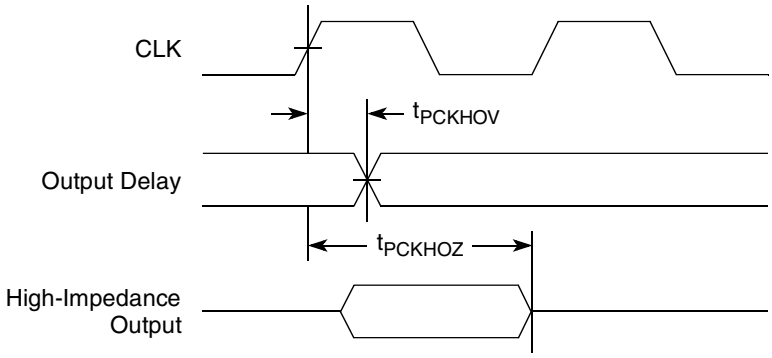


Figure 56. PCI Output AC Timing Measurement Condition

2.20 High-Speed Serial Interfaces

This chip features two Serializer/Deserializer (SerDes) interfaces to be used for high-speed serial interconnect applications. The SerDes1 interface is dedicated for PCI Express data transfers. The SerDes2 can be used for SGMII or SATA.

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes Reference Clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

2.20.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 57 shows how the signals are defined. For illustration purposes, only one SerDes lane is used for description. The figure shows waveform for either a transmitter output (SDn_TX and $\overline{\text{SDn\_TX}}$) or a receiver input (SDn_RX and $\overline{\text{SDn\_RX}}$). Each signal swings between A Volts and B Volts where A > B.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

1. **Single-Ended Swing**

The transmitter output signals and the receiver input signals SDn_TX, $\overline{\text{SDn\_TX}}$, SDn_RX and $\overline{\text{SDn\_RX}}$ each have a peak-to-peak swing of A - B Volts. This is also referred as each signal wire's Single-Ended Swing.

2. **Differential Output Voltage, V_{OD}** (or **Differential Output Swing**):

The Differential Output Voltage (or Swing) of the transmitter, V_{OD}, is defined as the difference of the two complimentary output voltages: V_{SDn_TX} - $V_{\overline{SDn\_TX}}$. The V_{OD} value can be either positive or negative.

3. **Differential Input Voltage, V_{ID}** (or **Differential Input Swing**):

The Differential Input Voltage (or Swing) of the receiver, V_{ID}, is defined as the difference of the two complimentary input voltages: V_{SDn_RX} - $V_{\overline{SDn\_RX}}$. The V_{ID} value can be either positive or negative.

4. **Differential Peak Voltage, V_{DIFFp}**

The peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak Voltage, V_{DIFFp} = |A - B| Volts.

5. **Differential Peak-to-Peak, $V_{DIFFp-p}$**

Since the differential output signal of the transmitter and the differential input signal of the receiver each range from A - B to -(A - B) Volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak-to-Peak Voltage, $V_{DIFFp-p} = 2*V_{DIFFp} = 2 * |(A - B)|$ Volts, which is twice of differential swing in amplitude, or twice of the differential

2.20.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the chip's SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below.

- **Differential Mode**
  - The input amplitude of the differential clock must be between 400mV and 1600mV differential peak-peak (or between 200mV and 800mV differential peak). In other words, each signal wire of the differential pair must have a single-ended swing less than 800mV and greater than 200mV. This requirement is the same for both external DC-coupled or AC-coupled connection.
  - For **external DC-coupled** connection, as described in Section 2.20.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 mV and 400 mV. Figure 59 shows the SerDes reference clock input requirement for DC-coupled connection scheme.
  - For **external AC-coupled** connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to SnGND. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage (SnGND). Figure 60 shows the SerDes reference clock input requirement for AC-coupled connection scheme.
- **Single-ended Mode**
  - The reference clock can also be single-ended. The SDn_REF_CLK input amplitude (single-ended swing) must be between 400mV and 800mV peak-peak (from Vmin to Vmax) with $\overline{\text{SDn\_REF\_CLK}}$ either left unconnected or tied to ground.
  - The SDn_REF_CLK input average voltage must be between 200 and 400 mV. Figure 61 shows the SerDes reference clock input requirement for single-ended signaling mode.
  - To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC-coupled externally. For the best noise performance, the reference of the clock could be DC or AC-coupled into the unused phase ($\overline{\text{SDn\_REF\_CLK}}$) through the same source impedance as the clock input (SDn_REF_CLK) in use.

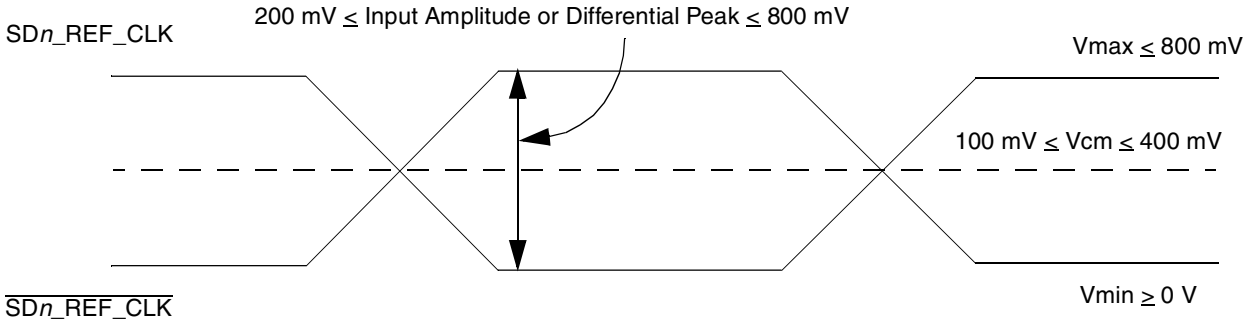


Figure 59. Differential Reference Clock Input DC Requirements (External DC-Coupled)

2.21 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the chip.

2.21.1 DC Requirements for PCI Express SD1_REF_CLK and $\overline{\text{SD1\_REF\_CLK}}$

For more information, see Section 2.20.2, "SerDes Reference Clocks."

2.21.2 AC Requirements for PCI Express SerDes Clocks

This table lists AC requirements.

Table 70. SD1_REF_CLK and $\overline{\text{SD1\_REF\_CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typical	Max	Units	Notes
t_{REF}	REFCLK cycle time	—	10	—	ns	1
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location	–50	—	50	ps	1,2,3

Notes:
1. Tj at BER of 10E-6 86 ps Max.
2. Total peak-to-peak deterministic jitter "Dj" should be less than or equal to 42 ps.
3. Limits from "PCI Express CEM Rev 2.0" and measured per "PCI Express Rj, D, and Bit Error Rates".

2.21.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million 15 (ppm) of each other at all times. This is specified to allow bit rate clock sources with a +/– 300 ppm tolerance.

2.21.4 Physical Layer Specifications

The following is a summary of the specifications for the physical layer of PCI Express on this chip. For further details as well as the specifications of the transport and data link layer, please use the PCI Express Base Specification. REV. 1.0a document.

2.21.4.1 Differential Transmitter (TX) Output

This table defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

Table 71. Differential Transmitter (TX) Output Specifications

Symbol	Parameter	Min	Nom	Max	Units	Comments
UI	Unit Interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for Spread Spectrum Clock dictated variations. See Note 1.
$V_{TX\text{-}DIFFp\text{-}p}$	Differential Peak-to-Peak Output Voltage	0.8	—	1.2	V	$V_{TX\text{-}DIFFp\text{-}p} = 2*\lvert V_{TX\text{-}D+} - V_{TX\text{-}D-}\rvert$ See Note 2.

2.23.1 Clock Ranges

This table provides the clocking specifications for the processor cores and Table 74 provides the clocking specifications for the memory bus.

Table 73. Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency								Unit	Notes
	600 MHz		800 MHz		1000 MHz		1250 MHz			
	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	600	600	600	800	600	1000	600	1250	MHz	1, 2
CCB frequency	400	400	400	400	333	400	333	500		
DDR Data Rate	400	400	400	400	400	400	400	500		

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, “CCB/SYSCLK PLL Ratio,” Section 2.23.3, “e500 Core PLL Ratio,“and Section 2.23.4, “DDR/DDRCLK PLL Ratio,” for ratio settings.
2. The processor core frequency speed bins listed also reflect the maximum platform (CCB) and DDR data rate frequency supported by production test. Running CCB and/or DDR data rate higher than the limit shown above, although logically possible via valid clock ratio setting in some condition, is not supported.

The DDR memory controller can run in either synchronous or asynchronous mode. When running in synchronous mode, the memory bus is clocked relative to the platform clock frequency. When running in asynchronous mode, the memory bus is clocked with its own dedicated PLL. This table provides the clocking specifications for the memory bus.

Table 74. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	600, 800, 1000, 1250			
	Min	Max		
DDR Memory bus clock speed	200	250	MHz	1, 2, 3, 4

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, “CCB/SYSCLK PLL Ratio,” Section 2.23.3, “e500 Core PLL Ratio,” and Section 2.23.4, “DDR/DDRCLK PLL Ratio,” for ratio settings.
2. The Memory bus clock refers to the chip’s memory controllers’ MCK[0:5] and $\overline{\text{MCK}}$[0:5] output clocks, running at half of the DDR data rate.
3. In synchronous mode, the memory bus clock speed is half the platform clock frequency. In other words, the DDR data rate is the same as the platform (CCB) frequency. If the desired DDR data rate is higher than the platform (CCB) frequency, asynchronous mode must be used.
4. In asynchronous mode, the memory bus clock speed is dictated by its own PLL. See Section 2.23.4, “DDR/DDRCLK PLL Ratio.” The memory bus clock speed must be less than or equal to the CCB clock rate which in turn must be less than the DDR data rate.

Table 79. Package Thermal Characteristics (continued)

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Junction-to-ambient (@200 ft/min)	Four layer board (2s2p)	$R_{\theta JA}$	14	°C/W	1, 2
Junction-to-board thermal	—	$R_{\theta JB}$	10	°C/W	3
Junction-to-case thermal	—	$R_{\theta JC}$	< 0.1	°C/W	4

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 and JESD51-6 with the board (JESD51-9) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the active surface of the die and the case top surface determined by the cold plate method (MIL SPEC-883 Method 1012.1) with the calculated case temperature. Actual thermal resistance is less than 0.1 •C/W

Simulations with heat sinks were done with the package mounted on the 2s2p thermal test board. The thermal interface material was a typical thermal grease such as Dow Corning 340 or Wakefield 120 grease.For system thermal modeling, the chip's thermal model without a lid is shown in Figure 72 The substrate is modeled as a block 29 x 29 x 1.2 mm with an in-plane conductivity of 19.8 W/m•K and a through-plane conductivity of 1.13 W/m•K. The solder balls and air are modeled as a single block 29 x 29 x 0.5 mm with an in-plane conductivity of 0.034 W/m•K and a through plane conductivity of 12.1 W/m•K. The die is modeled as 9.6 x 9.57 mm with a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate assuming a conductivity of 7.5 W/m•K in the thickness dimension of 0.07 mm. The die is centered on the substrate. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.

2.24.2 Recommended Thermal Model

This table shows the chip's thermal model.

Table 80. Thermal Model

Conductivity	Value	Units
Die (9.6x9.6 × 0.85 mm)		
Silicon	Temperature dependent	—
Bump/Underfill (9.6 x 9.6 × 0.07 mm) Collapsed Thermal Resistance		
Kz	7.5	W/m•K
Substrate (29 × 29 × 1.2 mm)		
Kx	19.8	W/m•K
Ky	19.8	
Kz	1.13	
Solder and Air (29 × 29 × 0.5 mm)		
Kx	0.034	W/m•K
Ky	0.034	
Kz	12.1	

The following pins must be connected to XGND if not used:

- SD1_RX[7:4]
- $\overline{\text{SD1\_RX[7:4]}}$
- SD1_REF_CLK
- $\overline{\text{SD1\_REF\_CLK}}$

3.11.3 SerDes 2 Interface Entirely Unused

If the high-speed SerDes 2 interface (SGMII/ SATA) is not used at all, the unused pin should be terminated as described in this section. There are several Reserved pins that need to be either left floating or connected to X2GND. See SerDes2 in Table 1Table 1 for details.

The following pins must be left unconnected (float):

- SD2_TX[0]
- $\overline{\text{SD2\_TX[0]}}$
- Reserved pins L8, L9

The following pins must be connected to X2GND:

- SD2_RX[0]
- $\overline{\text{SD2\_RX[0]}}$
- SD2_REF_CLK
- $\overline{\text{SD2\_REF\_CLK}}$

The POR configuration pin cfg_srds2_prtcl[0:2] on TSEC1_TXD[2], TSEC3_TXD[2], TSEC_1588_PUSLE_OUT1 can be used to power down SerDes 2 block for power saving. Note that both S2VDD and X2VDD must remain powered.

4 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in Section 4.1, “Part Numbers Fully Addressed by this Document.”

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